

PERFORMANCE SPECIFICATION

SEMICONDUCTOR DEVICE, FIELD EFFECT RADIATION HARDENED
(TOTAL DOSE AND SINGLE EVENT EFFECTS)
TRANSISTOR, N-CHANNEL, SILICON TYPES 2N7482T3, 2N7483T3 AND 2N7484T3
JANTXVR, F, G AND H AND JANSR, F, G AND H

This specification is approved for use by all Departments and Agencies of the Department of Defense.

1. SCOPE

1.1 Scope. This specification covers the performance requirements for an N-Channel, enhancement-mode, MOSFET, radiation hardened (total dose and Single Event Effects (SEE)), power transistor. Two levels of product assurance are provided for each device type as specified in MIL-PRF-19500, with avalanche energy maximum rating (E_{AS}) and maximum avalanche current (I_{AS}).

1.2 Physical dimensions. See figure 1, (TO-257AA, T3).

1.3 Maximum ratings. $T_A = +25^\circ\text{C}$, unless otherwise specified.

Type	P_T (1) $T_C = +25^\circ\text{C}$	P_T (1) $T_A = +25^\circ\text{C}$	V_{DS}	V_{DG}	V_{GS}	I_{D1} (2) $T_C = +25^\circ\text{C}$	I_{D2} (2) $T_C = +100^\circ\text{C}$	I_S	I_{DM} (3)	T_J and T_{STG}
	<u>W</u>	<u>W</u>	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A (pk)</u>	<u>°C</u>
2N7482T3	75	1.56	30	30	± 20	18	18	18	72	-55
2N7483T3			60	60	± 20	18	18	18	72	to
2N7484T3			100	100	± 20	18	14	18	72	+150

(1) Derate linearly $0.6 \text{ W}/^\circ\text{C}$ for $T_C > +25^\circ\text{C}$; $P_T = (T_{jmax} - T_C)/R_{\theta JC}$

(2) $I_D = ((T_{jmax} - T_C)/(R_{\theta JC}) \times (r_{DS(on)} \text{ at } T_{jmax}))^{1/2}$

(3) $I_{DM} = 4 \times I_{D1}$; I_{D1} as calculated by note (2)

1.4 Primary electrical characteristics at $T_C = +25^\circ\text{C}$.

Type	Min $V_{(BR)DSS}$ $V_{GS} = 0$ $I_D = 1.0 \text{ mA}$ dc	$V_{GS(TH)1}$ $V_{DS} \geq V_{GS}$ $I_D = 1.0 \text{ mA}$ dc	Max I_{DSS1} $V_{GS} = 0$ $V_{DS} = 80$ percent of rated V_{DS}	Max $r_{DS(on)}$ (1) $V_{GS} = 12 \text{ V}$, $I_D = I_{D2}$		$R_{\theta JC}$ Max	E_{AS}
				$T_J = +25^\circ\text{C}$	$T_J = +150^\circ\text{C}$		
	<u>V dc</u>	<u>V dc</u> Min Max	<u>μA dc</u>	<u>Ω</u>	<u>Ω</u>	<u>°C/W</u>	<u>mJ</u>
2N7482T3	30	2.0 4.0	10	0.030	0.060	1.67	177
2N7483T3	60			0.040	0.080		110
2N7484T3	100			0.070	0.140		87

(1) Pulsed (see 4.5.1).

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Defense Supply Center Columbus, ATTN: DSCC-VAC, P.O.Box 3990, Columbus, OH 43216-5000, by using the Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements documents cited in sections 3 and 4 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DODISS) and supplement thereto, cited in the solicitation (see 6.2).

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

STANDARD

DEPARTMENT OF DEFENSE

MIL-STD-750 - Test Methods for Semiconductor Devices.

(Unless otherwise indicated, copies of the above specifications, standards, and handbooks are available from the Defense Automated Printing Service, Building 4D (DPM-DODSSP), 700 Robbins Avenue, Philadelphia, PA 19111-5094.)

3. REQUIREMENTS

3.1 General. The requirements for acquiring the product described herein shall consist of this document and MIL-PRF-19500.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see 4.2 and 6.3).

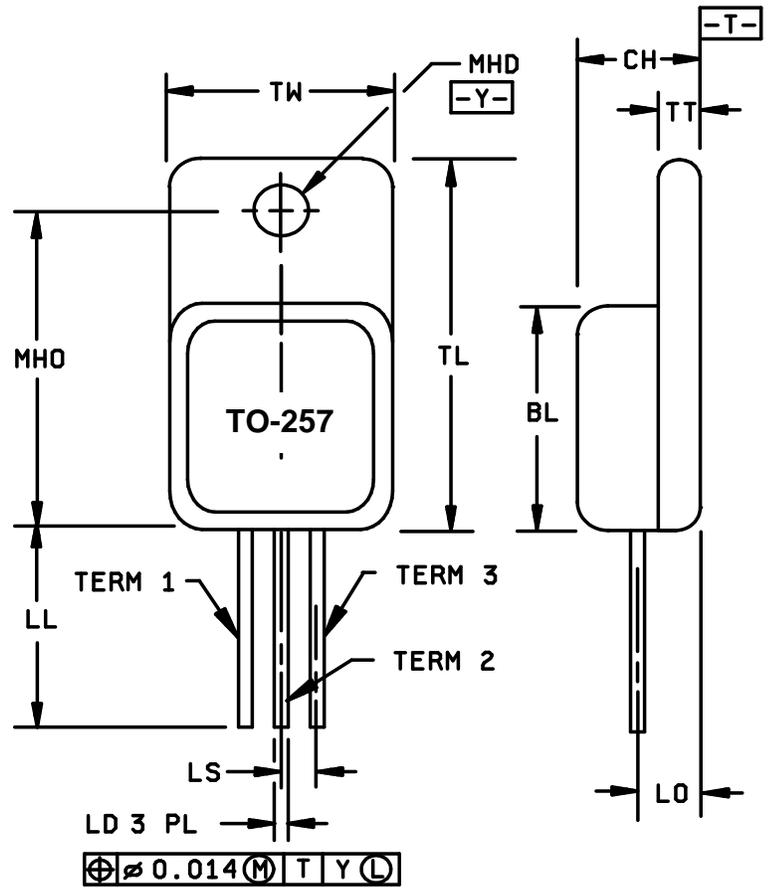
3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500.

3.4 Interface and physical dimensions. The interface and physical dimensions shall be as specified in MIL-PRF-19500 and on figure 1 (TO-257AA, T3) herein.

3.4.1 Lead finish. Unless otherwise specified, lead finish shall be solderable in accordance with MIL-PRF-19500, MIL-STD-750, and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

3.5 Electrostatic discharge protection. The devices covered by this specification require electrostatic discharge protection.

Symbol	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.410	.420	10.41	10.67
CH	.190	.200	4.83	5.08
LD	.025	.035	0.64	0.89
LL	.600	.650	15.24	16.51
LO	.120		3.05	
LS	.100 BSC		2.54	
MHD	.140	.150	3.56	3.81
MHO	.527	.537	13.38	13.64
TL	.645	.665	16.38	16.89
TT	.035	.045	.889	1.14
TW	.410	.420	10.41	10.67
TERM 1	Drain			
TERM 2	Source			
TERM 3	Gate			



NOTES:

1. Dimensions are in inches.
2. Metric equivalents are given for general information only.
3. All terminals are isolated from case.
4. In accordance with ANSI Y14.5M, diameters are equivalent to ϕ x symbology.

FIGURE 1. Dimensions and configuration (T0-257AA, T3).

3.5.1 Handling. MOS devices must be handled with certain precautions to avoid damage due to the accumulation of static charge. However, the following handling practices are recommended (see 3.5).

- a. Devices should be handled on benches with conductive handling devices.
- b. Ground test equipment, tools, and personnel handling devices.
- c. Do not handle devices by the leads.
- d. Store devices in conductive foam or carriers.
- e. Avoid use of plastic, rubber, or silk in MOS areas.
- f. Maintain relative humidity above 50 percent if practical.
- g. Care should be exercised during test and troubleshooting to apply not more than maximum rated voltage to any lead.
- h. Gate must be terminated to source, $R \leq 100 \text{ k}$, whenever bias voltage is to be applied drain to source.

3.6 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3, 1.4, and table I herein.

3.7 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table I herein.

3.8 Marking. Marking shall be in accordance with MIL-PRF-19500.

3.9 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4, table I, II and III).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500. Alternate flow is allowed for qualification inspection in accordance with figure 4 of MIL-PRF-19500.

4.2.1 Group E inspection. Group E inspection shall be conducted in accordance with MIL-PRF-19500, and table III herein.

4.2.1.1 SEE. Design capability shall be tested on the initial qualification and thereafter whenever a major die design or process change is introduced. See design safe operation area figures 2, 3, 4 and 5 herein. End-point measurements shall be in accordance with table III.

4.3 Screening (JANS, JANTX, and JANTXV). Screening shall be in accordance with table IV of MIL-PRF-19500, and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see table IV of MIL-PRF-19500)	Measurement	
	JANS	JANTX and JANTXV
(1)	Method 3470 of MIL-STD-750, E _{AS} test (see 4.5.4)	Method 3470 of MIL-STD-750, E _{AS} test (see 4.5.4)
(1)	Method 3161 of MIL-STD-750, thermal impedance (see 4.5.3)	Method 3161 of MIL-STD-750, thermal impedance (see 4.5.3)
(1)	Gate stress test (see 4.5.5)	Gate stress test (see 4.5.5)
(2) 9	Subgroup 2 of table I herein I _{DSS1} , I _{GSS} as a minimum	Not applicable
10	Method 1042 of MIL-STD-750, Test condition B	Method 1042 of MIL-STD-750, test condition B
11	I _{GSSF1} , I _{GSSR1} , I _{DSS1} , r _{DS(ON)} , V _{GS(TH)} Subgroup 2 of table I herein. $\Delta I_{GSSF1} = \pm 20 \text{ nA dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta I_{GSSR1} = \pm 20 \text{ nA dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta I_{DSS1} = \pm 10 \text{ } \mu\text{A dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$	I _{GSSF1} , I _{GSSR1} , I _{DSS1} , r _{DS(ON)} , V _{GS(TH)} Subgroup 2 of table I herein.
12	Method 1042 of MIL-STD-750, test condition A	Method 1042 of MIL-STD-750, test condition A
13	Subgroups 2 and 3 of table I herein $\Delta I_{GSSF1} = \pm 20 \text{ nA dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta I_{GSSR1} = \pm 20 \text{ nA dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta I_{DSS1} = \pm 10 \text{ } \mu\text{A dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta r_{DS(ON)1} = \pm 20 \text{ percent of initial value.}$ $\Delta V_{GS(TH)1} = \pm 20 \text{ percent of initial value.}$	Subgroups 2 and 3 of table I herein $\Delta I_{GSSF1} = \pm 20 \text{ nA dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta I_{GSSR1} = \pm 20 \text{ nA dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta I_{DSS1} = \pm 10 \text{ } \mu\text{A dc or } \pm 100 \text{ percent of initial value, whichever is greater.}$ $\Delta r_{DS(ON)1} = \pm 20 \text{ percent of initial value.}$ $\Delta V_{GS(TH)1} = \pm 20 \text{ percent of initial value.}$

(1) Shall be performed anytime before screen 10.

(2) Shall be performed after E_{AS} test, thermal impedance test, and gate stress test.

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500. Alternate flow is allowed for conformance inspection in accordance with figure 4 of MIL-PRF-19500.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with table V of MIL-PRF-19500 and table I herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VIa (JANS) and table VIb (JANTX and JANTXV) of MIL-PRF-19500, and as follows. Electrical measurements (end-points) shall be in accordance with table I, group A, subgroup 2 herein.

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4.4.2.1 Group B inspection, table VIa (JANS) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B3	1051	Test condition G, 100 cycles.
B3	2077	SEM (Scanning Electron Microscope).
B4	1042	Intermittent operation life, condition D, 2,000 cycles. No heat sink or forced-air cooling on the device shall be permitted during the on cycle. $t_{on} = 30$ seconds minimum.
B5	1042	Accelerated steady-state gate bias, condition B, $V_{GS} = \text{rated}$; $T_A = +175^\circ\text{C}$, $t = 24$ hours minimum; or $T_A = +150^\circ\text{C}$, $t = 48$ hours minimum.
B5	1042	Accelerated steady-state reverse bias, condition A, $V_{DS} = \text{rated}$; $T_A = +175^\circ\text{C}$, $t = 120$ hours minimum; or $T_A = +150^\circ\text{C}$, $t = 240$ hours minimum.
B5	2037	Bond strength (Al-Au die interconnects only), test condition A.
B6	3161	Thermal resistance, see 4.5.2.

4.4.2.2 Group B inspection, table VIb (JANTX and JANTXV) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B2	1051	Test condition G, 25 cycles.
B3	1042	Intermittent operation life, condition D, 2,000 cycles. No heat sink or forced-air cooling on the device shall be permitted during the on cycle. $t_{on} = 30$ seconds minimum.
B5 and B6		Not applicable.

4.4.2.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VII of MIL-PRF-19500 and as follows. Electrical measurements (end-points) shall be in accordance with table I, group A, subgroup 2 herein.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
C2	2036	Terminal strength is not applicable.
C6	1042	Intermittent operation life, condition D, 2,000 cycles. No heat sink or forced-air cooling on the device shall be permitted during the on cycle. $t_{on} = 30$ seconds minimum.

4.4.3 Group D inspection. Group D inspection shall be conducted in accordance with table VIII of MIL-PRF-19500 and table II herein.

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

4.5.2 Thermal resistance. Thermal resistance measurements shall be performed in accordance with method 3161 of MIL-STD-750. The maximum limit of $R_{\theta JC} = 1.67 \text{ }^\circ\text{C/W}$. The following parameters shall apply:

- a. Measuring current (I_M).....10 mA.
- b. Drain heating current (I_H).....4.20 A.
- c. Heating time (t_H).....Steady-state (see Method 3161 of MIL-STD-750).
- d. Drain-source heating voltage (V_H).....12 V.
- e. Measurement time delay (t_{MD}).....30 to 60 μs .
- f. Sample window time (t_{SW}).....10 μs maximum.

4.5.3 Thermal response ($Z_{\theta JC}$ measurement). The $Z_{\theta JC}$ measurement (or equivalent ΔV_{SD} measurement) shall be performed in accordance with method 3161 of MIL-STD-750. The maximum limit (not to exceed figure 6, thermal impedance curves and the group A, subgroup 2 limits) for $Z_{\theta JC}$ in screening (table IV of MIL-PRF-19500) shall be derived by each vendor by means of statistical process control. When the process has exhibited control and capability, the capability data shall be used to establish the fixed limit. In addition to screening, once a fixed limit has been established, monitor all future sealing lots using a random five piece sample from each lot, to be plotted on the applicable X and R chart. If a lot exhibits an out of control condition, the entire lot shall be removed from the line and held for engineering evaluation and disposition. This procedure may be used in lieu of an in line process monitor.

- a. Measuring current (I_M).....10 mA.
- b. Drain heating current (I_H).....4.20 A.
- c. Heating time (t_H).....50 ms.
- d. Drain-source heating voltage (V_H).....12 V.
- e. Measurement time delay (t_{MD}).....30 - 60 μs .
- f. Sample window time (t_{SW}).....10 μs maximum.

4.5.4 Single pulse avalanche energy (E_{AS}).

- a. Peak current, $I_{AS} = I_{D1}$.
- b. Inductance, $L = (2 * E_{AS} / (I_{D1})^2) * ((V_{BR} - V_{DD}) / V_{BR})$ mH minimum.
- c. Gate to source resistor, R_{GS} : $25 \text{ } \Omega \leq R_{GS} \leq 200 \text{ } \Omega$.
- d. Supply voltage, $V_{DD} = 25 \text{ V dc}$, except $V_{DD} = 50 \text{ V dc}$ for 2N7484T3.
- e. Initial case temperature, $T_C = +25^\circ \text{C}$, -5°C , $+10^\circ \text{C}$.
- f. Gate voltage, $V_{GS} = 12 \text{ V dc}$.
- g. Number of pulses to be applied: 1 pulse minimum.

4.5.5 Gate stress test.

- a. $V_{GS} = 24 \text{ V}$, minimum.
- b. $t = 250 \text{ } \mu\text{s}$, minimum.

TABLE I. Group A inspection.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Condition		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical inspection	2071					
<u>Subgroup 2</u>						
Thermal impedance <u>2/</u>	3161	See 4.5.3	$Z_{\theta JC}$	1.35		°C/W
Breakdown voltage drain to source	3407	$V_{GS} = 0V$, $I_D = 1 \text{ mA dc}$, bias condition C	$V_{(BR)DSS}$			
2N7482T3				30		V dc
2N7483T3				60		V dc
2N7484T3				100		V dc
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS}$, $I_D = 1 \text{ mA dc}$	$V_{GS(TH)1}$	2.0	4.0	V dc
Gate current	3411	$V_{GS} = \pm 20V \text{ dc}$, bias condition C, $V_{DS} = 0V$	I_{GSS1}		± 100	nA dc
Drain current	3413	$V_{GS} = 0V \text{ dc}$, bias condition C, $V_{DS} = 80 \text{ percent of rated } V_{DS}$,	I_{DSS1}		10	$\mu\text{A dc}$
Static drain to source "on" state resistance	3421	$V_{GS} = 12V \text{ dc}$, condition A, pulsed (see 4.5.1), $I_D = I_{D2}$	$r_{DS(ON)1}$			
2N7482T3					0.030	Ω
2N7483T3					0.040	Ω
2N7484T3					0.070	Ω
Forward voltage	4011	$V_{GS} = 0 \text{ V dc}$, condition A, pulsed (see 4.5.1), $I_D = I_{D1}$	V_{SD}			
2N7482T3					1.2	V dc
2N7483T3					1.2	V dc
2N7484T3					1.2	V dc

See footnotes at end of table.

TABLE I. Group A inspection – Continued.

Inspection 1/	MIL-STD-750		Symbol	Limits		Unit
	Method	Condition		Min	Max	
<u>Subgroup 3</u>						
High temperature operation						
$T_C = T_J = +125^\circ\text{C}$						
Gate current	3411	$V_{GS} = \pm 20\text{V dc}$, bias condition C, $V_{DS} = 0\text{ V}$	I_{GSS2}		± 200	nA dc
Drain current	3413	$V_{GS} = 0\text{ V dc}$, bias condition C, $V_{DS} = 80$ percent of rated V_{DS}	I_{DSS2}		25	$\mu\text{A dc}$
Static drain to source "on"- state resistance	3421	$V_{GS} = 12\text{V dc}$, condition A, pulsed (see 4.5.1), $I_D = I_{D2}$	$r_{DS(ON)3}$			
2N7482T3					0.060	Ω
2N7483T3					0.080	Ω
2N7484T3					0.140	Ω
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS}$, $I_D = 1\text{ mA dc}$	$V_{GS(TH)2}$	1.0		V dc
Low temperature operation						
$T_C = T_J = -55^\circ\text{C}$						
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS(TH)3}$, $I_D = 1\text{ mA dc}$	$V_{GS(TH)3}$		5.0	V dc
<u>Subgroup 4</u>						
Forward transconductance	3475	$I_D = I_{D2}$, $V_{DD} = 15\text{ V dc}$ (See 4.5.1)	g_{FS}			
2N7482T3				16		S
2N7483T3				16		S
2N7484T3				13		S
Switching time test	3472	$I_D = I_{D2}$, $V_{GS} = 12\text{ V dc}$, $R_G = 2.35\Omega$, $V_{DD} = 50$ percent of rated V_{DS}				
Turn-on delay time			$t_{D(on)}$		25	ns
Rise time			t_r		100	ns
Turn-off delay time			$t_{D(off)}$		35	ns
Fall time			t_f		30	ns

See footnotes at end of table.

TABLE I. Group A inspection – Continued.

Inspection 1/	MIL-STD-750		Symbol	Limits		Unit			
	Method	Condition		Min	Max				
<u>Subgroup 5</u> Safe operating area test (high voltage)	3474	See figures 3, 4 and 5 $t_p = 10$ ms min. $V_{DS} = 80$ percent of max. rated V_{DS}							
Electrical measurements							See table I, group A, subgroup 2		
<u>Subgroup 6</u> Not applicable									
<u>Subgroup 7</u> Gate charge	3471	Condition B. $I_D = I_{D2}$, $V_{GS} = 12$ V dc $V_{DD} = 50$ percent of rated V_{DS}							
On-state gate charge							$Q_{G(ON)}$		
2N7482T3								65	nC
2N7483T3								45	nC
2N7484T3								50	nC
Gate to source charge							Q_{GS}		
2N7482T3								20	nC
2N7483T3								10	nC
2N7484T3								7.4	nC
Gate to drain charge							Q_{GD}		
2N7482T3		10	nC						
2N7483T3		15	nC						
2N7484T3		20	nC						
Reverse recovery time	3473	$di/dt = -100$ A/ μ s, $V_{DD} \leq 50$ V $I_D = I_{D2}$							
2N7482T3								102	ns
2N7483T3								99	ns
2N7484T3								250	ns

1/ For sampling plan, see MIL-PRF-19500.

2/ This test required for the following endpoint measurements only:

Group B, subgroups 2 and 3 (JANTX/JANTXV).

Group B, subgroups 3 and 4 (JANS).

Group C, subgroup 6.

Group E, subgroup 1.

TABLE II Group D inspection.

Inspection <u>1/ 2/ 3/</u>	MIL-STD-750		Symbol	Pre-irradiation limits		Post-irradiation limits			Unit	
	Method	Conditions		R, F, G and H		R, F and G		H <u>4/</u>		
				Min	Max	Min	Max	Min		Max
<u>Subgroup 1</u> Not applicable										
<u>Subgroup 2</u>		$T_C = +25^\circ\text{C}$								
Steady-state total dose irradiation (VGS bias) <u>5/</u>	1019	$V_{GS} = 12\text{ V};$ $V_{DS} = 0\text{ V}$								
Steady-state total dose irradiation (VDS bias) <u>5/</u>	1019	$V_{GS} = 0\text{ V};$ $V_{DS} = 80\text{ percent of rated}$ $V_{DS}(\text{preirradiation})$								
End-point electricals										
Breakdown voltage, drain to source 2N7482T3 2N7483T3 2N7484T3	3407	$V_{GS} = 0\text{ V}; I_D = 1\text{ mA};$ bias condition C	$V_{(BR)DSS}$	30 60 100		30 60 100		30 60 100	V dc V dc V dc	
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS}$ $I_D = 1\text{ mA}$	$V_{GS(th)1}$	2.0	4.0	2.0	4.0	1.5	4.0	V dc
Gate current	3411	$V_{GS} = +20\text{ V}; V_{DS} = 0\text{ V},$ bias condition C	I_{GSSF1}		100		100		100	nA dc
Gate current	3411	$V_{GS} = -20\text{ V}; V_{DS} = 0\text{ V},$ bias condition C	I_{GSSR1}		-100		-100		-100	nA dc
Drain current	3413	$V_{GS} = 0\text{ V}$ $V_{DS} = 80\text{ percent of rated}$ $V_{DS}(\text{preirradiation}),$ bias condition C	I_{DSS}		10		10		10	$\mu\text{A dc}$
Static drain to source on-state voltage 2N7482T3 2N7483T3 2N7484T3	3405	$V_{GS} = 12\text{ V}; I_D = I_{D2}$ Condition A, pulsed (see 4.5.1)	$V_{DS(on)}$		0.540 0.720 0.980		0.450 0.720 0.980		0.630 0.864 1.190	V dc V dc V dc
Forward voltage source drain diode	4011	$V_{GS} = 0\text{ V}; I_D = I_{D1},$ bias condition C	V_{SD}		1.2		1.2		1.2	V dc

1/ For sampling plan see MIL-PRF-19500.

2/ Group D qualification may be performed prior to lot formation. Wafers qualified to these group D QCI requirements may be used for any other detail specification utilizing the same die design.

3/ At the manufacturer's option, group D samples need not be subjected to the screening tests, and may be assembled in its qualified package or in any qualified package that the manufacturer has data to correlate the performance to the designated package.

4/ The H designation represents devices which pass end-points at all 100K, 300K and 600K rads (Si).

5/ Separate samples shall be pulled for each bias.

TABLE III. Group E inspection (all quality levels) - for qualification only.

Inspection	MIL-STD-750		Qualification inspection
	Method	Conditions	
<u>Subgroup 1</u>			12 devices c = 0
Temperature cycling	1051	Test condition G, 500 cycles	
Hermetic seal	1071		
Fine leak			
Gross leak			
Electrical measurements		See table I, group A, subgroup 2	
<u>Subgroup 2 1/</u>			12 devices c = 0
Steady-state gate bias	1042	Test condition B; 1,000 hours	
Electrical measurements		See table I, group A, subgroup 2	
Steady-state reverse bias	1042	Test condition A; 1,000 hours	
Electrical measurements		See table I, group A, subgroup 2	
<u>Subgroup 3</u>			
Not applicable			
<u>Subgroup 4</u>			12 devices c = 0
Thermal resistance	3161	$R_{\theta JC} = 1.67^{\circ}\text{C/W}$ maximum. See 4.5.2	
<u>Subgroup 5</u>			
Not applicable			
<u>Subgroup 6</u>			3 devices c = 0
ESD	1020		
Electrical measurements		See table I, group A, subgroup 2	

See footnotes at end of table.

TABLE III. Group E inspection (all quality levels) for qualification only - Continued.

Inspection	MIL-STD-750		Qualification and large lot quality conformance inspection
	Method	Conditions	
<u>Subgroup 7</u>			3 devices
SEE <u>3/ 4/ 5/</u>	1080		
Electrical measurements <u>2/</u>		IGSS1 and IDSS1 in accordance with table I, group A, subgroup 2	
SEE irradiation		Fluence = $3E5 \pm 20$ percent ions/cm ² Flux = 2E3 to 2E4 ions/cm ² /sec, Temperature = 25 ± 5 °C	
2N7482T3		LET = 37 MeV-cm ² /mg, Range = 39 microns, Energy = 305 MeV Insitu bias conditions: VDS = 30V and VGS = -10V VDS = 25V and VGS = -15V VDS = 20V and VGS = -20V	
2N7483T3		Insitu bias conditions: VDS = 60V and VGS = -10V VDS = 52V and VGS = -15V VDS = 34V and VGS = -20V	
2N7484T3		Insitu bias conditions: VDS = 100V and VGS = -20V	
2N7482T3		LET = 60 MeV-cm ² /mg, Range = 32 microns, Energy = 340 MeV Insitu bias conditions: VDS = 25V and VGS = -5V VDS = 20V and VGS = -10V VDS = 15V and VGS = -15V VDS = 10V and VGS = -20V	
2N7483T3		Insitu bias conditions: VDS = 46V and VGS = -5V VDS = 35V and VGS = -10V VDS = 25V and VGS = -15V VDS = 15V and VGS = -20V	
2N7484T3		Insitu bias conditions: VDS = 100V and VGS = -10V VDS = 35V and VGS = -15V VDS = 25V and VGS = -20V	
2N7482T3		LET = 82 MeV-cm ² /mg, Range = 28 microns, Energy = 350 MeV Insitu bias conditions: VDS = 22.5V and VGS = -5V VDS = 15V and VGS = -10V VDS = 10V and VGS = -15V	
2N7483T3		Insitu bias conditions: VDS = 35V and VGS = -5V VDS = 27V and VGS = -10V VDS = 20V and VGS = -15V VDS = 14V and VGS = -20V	
2N7484T3		Insitu bias conditions: VDS = 100V and VGS = -5V VDS = 80V and VGS = -10V VDS = 25V and VGS = -15V	
Electrical measurements <u>2/</u>		IGSS1 and IDSS1 in accordance with table I, group A, subgroup 2	

1/ A separate sample for each test shall be pulled.

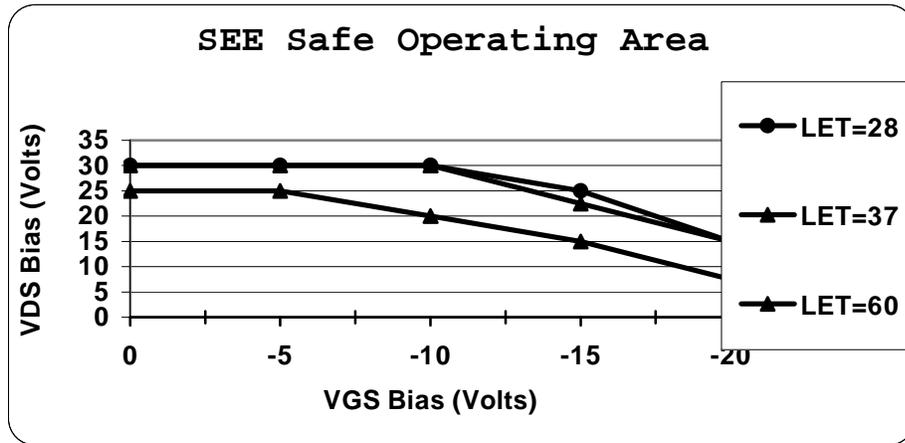
2/ Examine IGSS1 and IDSS1 before and following SEE irradiation to determine acceptability for each bias condition. Other test conditions in accordance with table I, group A, subgroup 2, may be performed at the manufacturer's option.

3/ Group E qualification of SEE testing may be performed prior to lot formation. Qualification may be extended to other performance specifications utilizing the same structurally identical die design.

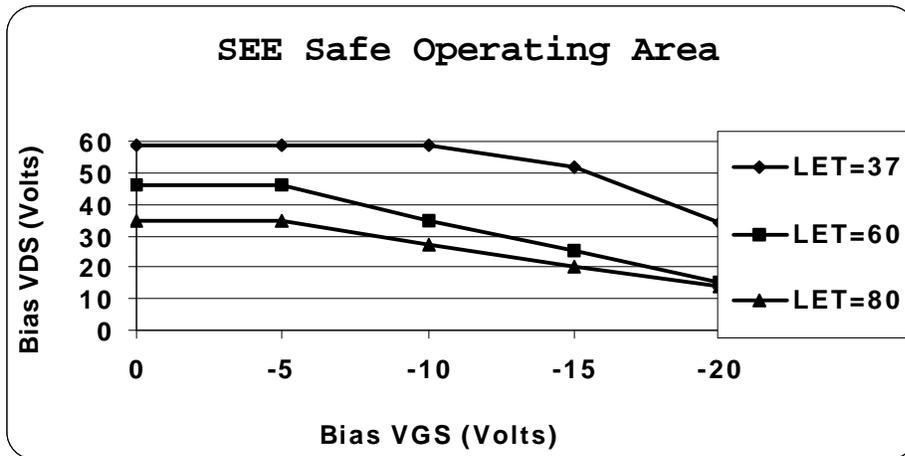
4/ Device qualification to a higher level LET is sufficient to qualify all lower level LET's.

5/ The sampling plan applies to each bias condition.

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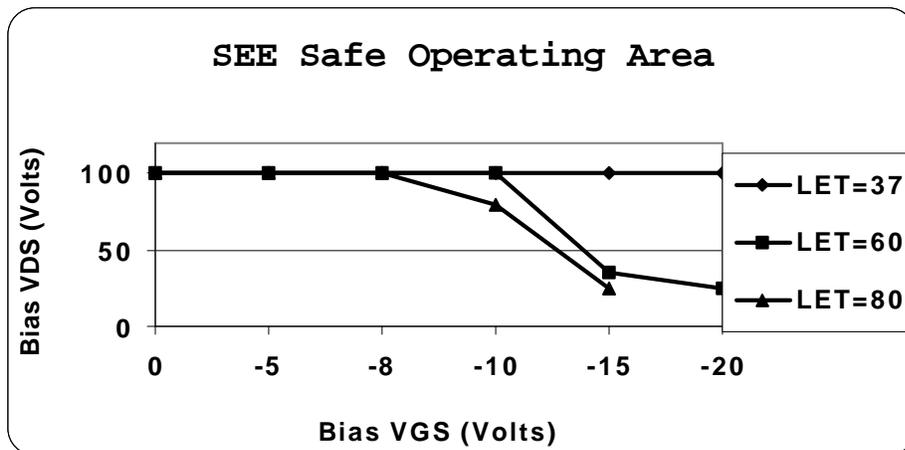
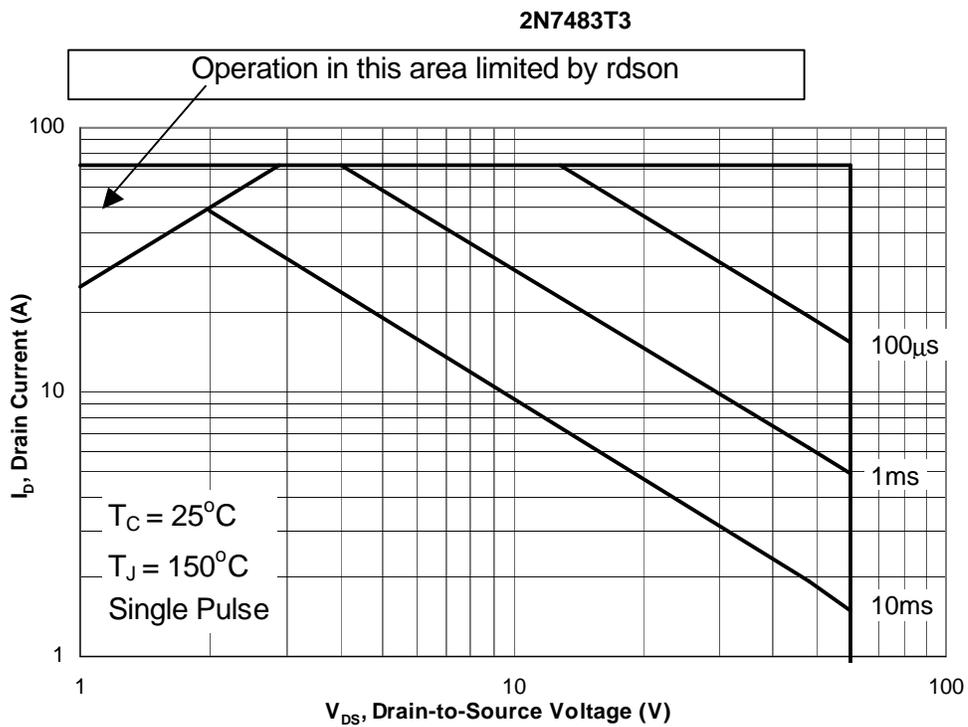
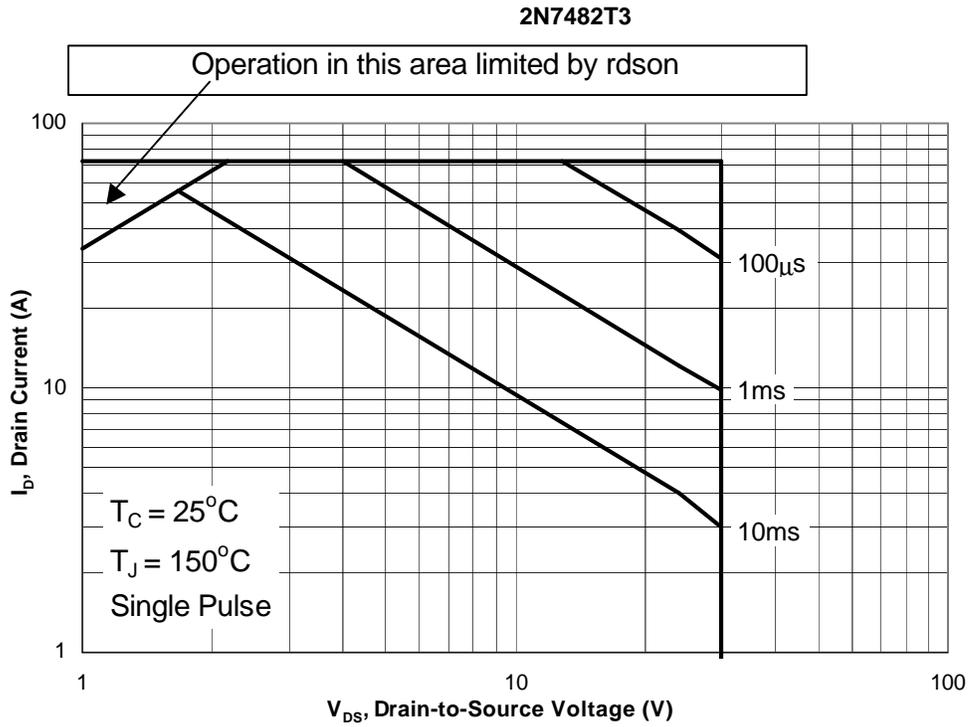


FIGURE 2. SEE safe operating area graph.



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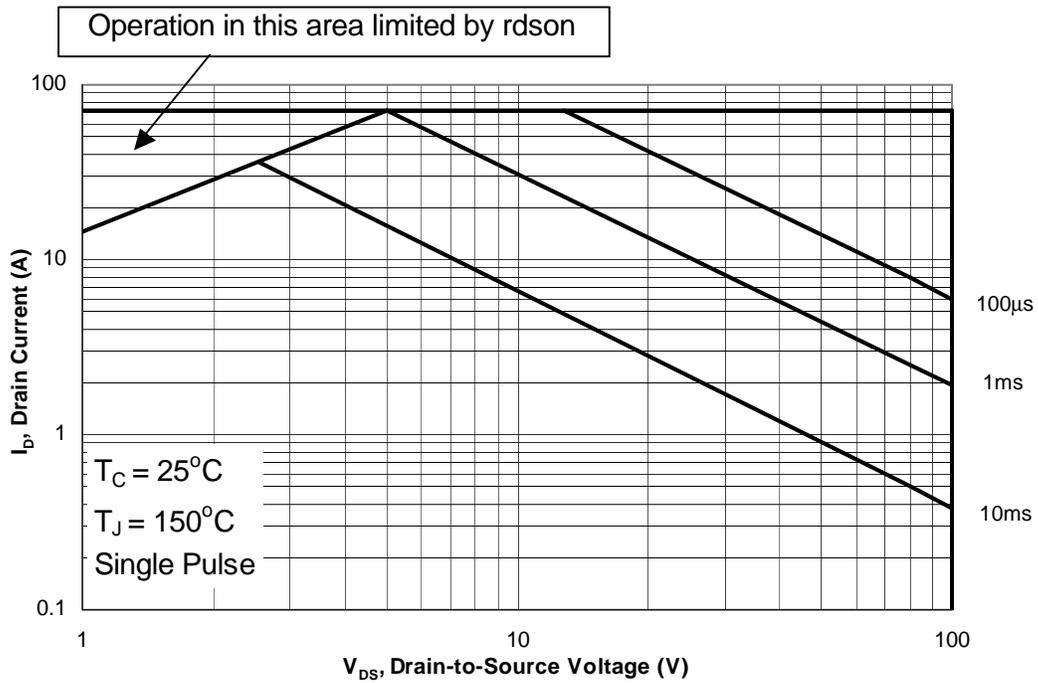


FIGURE 5. Safe operating area graph.

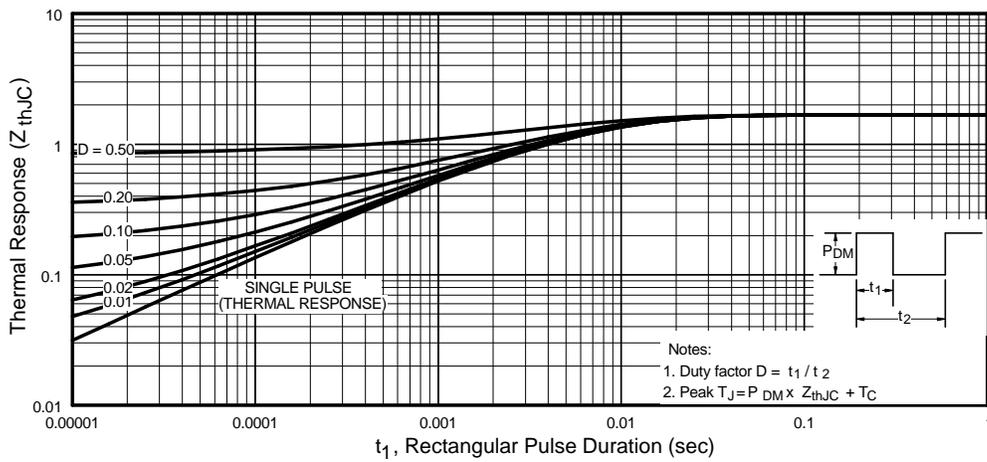


FIGURE 6. Thermal response curve.

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Points' packaging activity within the Military Department or Defense Agency, or within the Military Departments' System Command. Packaging data retrieval is available from the managing Military Departments' or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory.)

6.1 Intended use. The notes specified in MIL-PRF-19500 are applicable to this specification.

6.2 Acquisition requirements. Acquisition documents must specify the following:

- a. Title, number, and date of this specification.
- b. Issue of DoDISS to be cited in the solicitation, and if required, the specific issue of individual documents referenced (see 2.2.1).
- c. Lead finish (see 3.4.1).
- d. Packaging requirements (see 5.1).

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List QML-19500 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or purchase orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from Defense Supply Center, Columbus, ATTN: DSCC/VQE, P.O. Box 3990, Columbus, OH 43216-5000.

6.4 Cross-reference list. The following information shows the generic P/N and its associated military P/N (without JAN and RHA prefix).

Generic P/N	Military P/N
IRHY57Z30CM	2N7482T3
IRHY57034CM	2N7483T3
IRHY57130CM	2N7484T3

Custodians:
 Army - CR
 Navy - NW
 Air Force - 11
 NASA - NA
 DLA - CC

Preparing activity:
 DLA - CC
 (Project 5961-2519)

STANDARDIZATION DOCUMENT IMPROVEMENT PROPOSAL

INSTRUCTIONS

1. The preparing activity must complete blocks 1, 2, 3, and 8. In block 1, both the document number and revision letter should be given.
2. The submitter of this form must complete blocks 4, 5, 6, and 7.
3. The preparing activity must provide a reply within 30 days from receipt of the form.

NOTE: This form may not be used to request copies of documents, nor to request waivers, or clarification of requirements on current contracts. Comments submitted on this form do not constitute or imply authorization to waive any portion of the referenced document(s) or to amend contractual requirements.

I RECOMMEND A CHANGE:	1. DOCUMENT NUMBER MIL-PRF-19500/702	2. DOCUMENT DATE 28 November 2001
3. DOCUMENT TITLE SEMICONDUCTOR DEVICE, FIELD EFFECT RADIATION HARDENED (TOTAL DOSE AND SINGLE EVENT EFFECTS) TRANSISTOR, N-CHANNEL, SILICON TYPES 2N7482T3, 2N7483T3 AND 2N7484T3 JANTXVR, F, G AND H AND JANSR, F, G AND H		
4. NATURE OF CHANGE (Identify paragraph number and include proposed rewrite, if possible. Attach extra sheets as needed.)		
5. REASON FOR RECOMMENDATION		
6. SUBMITTER		
a. NAME (Last, First, Middle initial)	b. ORGANIZATION	
c. ADDRESS (Include Zip Code)	d. TELEPHONE (Include Area Code) COMMERCIAL DSN FAX EMAIL	7. DATE SUBMITTED
8. PREPARING ACTIVITY		
a. Point of Contact Alan Barone	b. TELEPHONE Commercial DSN FAX EMAIL 614-692-0510 850-0510 614-692-6939 alan.barone@dsccl.dla.mil	
c. ADDRESS Defense Supply Center Columbus, ATTN: DSCC-VAC, P.O. Box 3990, Columbus, OH 43216-5000	IF YOU DO NOT RECEIVE A REPLY WITHIN 45 DAYS, CONTACT: Defense Standardization Program Office (DLSC-LM) 8725 John J. Kingman, Suite 2533, Fort Belvoir, VA 22060-6221 Telephone (703) 767-6888 DSN 427-6888	